# IN SULATOR -M ETAL TRANSITION IN A CONSERVATIVE SYSTEM :AN EVIDENCE FOR MOBILITY COALESCENCE IN ISLAND SILVER FILM S

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#### Abstract:

Aging, which manifests itself as an irreversible increase in electrical resistance, in island metal Ims is of considerable interest from both academ ic as well as applications point of view. A ging is attributed to various causes, oxidation of islands and m obility of islands followed by coalescence (m obility coalescence) being the main contenders. The e ect of parameters like substrate tem perature, substrate cleaning, residual gases in the vacuum chamber, ultrasonic vibration of the substrate suggest that the mobility coalescence is responsible for the aging in island metal lm s. Electron microscopy studies show evidence for mobility of islands at high substrate tem peratures. The com parison of aging data of island silver Im s deposited on glass substrates in ultra high vacuum and high vacuum suggests that the oxidation of islands, as being responsible for aging in these In s, can be ruled out. Further, under certain conditions of deposition, island silver Im s exhibit a dram atic and drastic fall in electrical resistance, marking the insulator m etal transition. This interesting transition observed in a conservative system -after the stoppage of deposition of the lm - is a clear evidence for m obility coalescence of islands even at room tem perature. The sudden fall in resistance is preceded uctuations in resistance with time and the uctuations are attributed to by the making and breaking of the percolation path in the  $\mbox{ lm}$  .

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## Introduction:

Thin Im growth on any substrates occurs in one of the two broad categories of growth modes namely Layer by Layer growth mode or Stranski-K rastanov growth mode and island growth mode or Volmer-Weber growth mode. Surface and interfacial energies determine the growth mode of a Im. In general, vapor deposition of metal Ims on glass substrates grow by island mode. In the island mode, vapor atoms impinging on the substrate surface get adsorbed and are known as adatoms. These adatoms migrate on the substrate surface to form nuclei. When two nuclei touch each other they coalesce to form a larger cluster. As the deposition continues, at a particular surface coverage, a Large Scale Coalescence (LSC) takes place forming a network structure leaving holes and channels in between. Secondary nucleation in the holes and channels Il up to form a continuous Im.

Therefore, by limiting the growth of a lm to nucleation stage or by avoiding excessive coalescence island lms or discontinuous lms, consisting an array of discrete islands with statistical distribution of island radii and separations, can be obtained. A lthough, such lms have m any attractive properties, they cannot by exploited yet for device applications due to their inherent temporal instability or aging even in vacuum. A ging m anifests as an irreversible increase in their DC electrical resistance.

Aging Studies:

The expression for electrical resistance of an island  $\ln$  is exponentially dependent on the average inter-island spacing [1, 2] and aging is attributed to the increase in average island spacing following the stoppage of deposition. The increase in the average island spacing can come about by island shape changes [3], oxidation of islands [4] and m obility of islands followed by coalescence [5].

O xidation of islands m odel and m obility coalescence m odel are the m ain contenders in explaining the aging process in island m etal  $\ln s$ . Studies on the e ect of residual gases on the aging of island silver and copper  $\ln s$  through the quantic cation of the aging process indicated that oxidation m ight not be responsible for aging in these  $\ln s$  [6, 7]. The substrate temperature e ect too supported this view [8].

As the deposited m aterial in the lm is increased, the average island size increases and average island spacing decreases resulting in lower resistance of the lm. If m obility coalescence is operative, a reduced aging rate is expected for higher thickness or lower resistance lm s, as m obility is size dependent,

larger islands being less mobile. If the deposition continues, a LSC would occur and a very small aging rate is expected due to the incorporation of small islands to the network structure.

Table 1 shows typical coalescence rates, de ned as the change in tunneling length perm inute calculated over xed time interval [9], for silver lms under di erent conditions of ultrasonic vibrations of the substrate. Here, NV refers to no vibration of the substrate either during deposition or during aging. VD is the condition where in substrate is vibrated only during deposition. VA refers to the vibration only during aging [10]. It is clear from the table that the larger islands form ed due to vibration during deposition show lower coalescence rate as compared to NV condition. The lms form ed under sim ilar conditions show higher coalescence rate when the lms are subjected to vibration during aging (NV and VA). Further, lower initial resistance (resistance immediately after the deposition is stopped) lms show lower coalescence rate as they contain larger islands. These observations strongly support m obility coalescence m odel.

Initial Resistance	Coalescence Rates (A/min)		
	NV	VD	VA
2 M =	0.0656	0.0345	0.0889
10 M =	0.1284	0.08321	0.1566
20 M =	0.2209	0.1575	0.3179

Table 1 : Coalescence rates for silver island Im s under di erent conditions of substrate vibrations

The silver island lm s on glass substrates studied under a UHV of 2x10  $^8$ Torrwith an oxygen partial pressure of the order of 10  $^{11}$  Torr too show considerable aging for extended periods. Further, coalescence rates under UHV and HV of 2x10  $^6$  Torr { HV obtained using an oil di usion pump- are nearly the same [11]. These results further strengthen the mobility coalescence model.

## Insulator-M etal Transition:

It is well known that after the occurrence of LSC very little material is required to be deposited to form a semicontinuous lm with a connecting path between the electrodes being established. This is the discontinuous { sem icontinuous transition often term ed as insulator { m etal transition in the case of granular metal Ims. Island silver Ims deposited on glass substrates with an initial resistance of 2M =, at a deposition rate of 0.2A /sexhibits a very interesting behavior and is shown in Fig. 1. The Im shows a small aging rate for a few m inutes of aging. Then the resistance falls drastically, after which the resistance remains almost steady. The aging is characteristic of island or discontinuous Im s while a steady or a steady decrease in resistance with time is the property of a continuous or a sem icontinuous lm. The behavior exhibited by this Im clearly indicates an insulator { metal transition. The sm all aging rate observed before the transition indicates that the LSC stage has already been crossed for this lm. At a very low deposition rate of 0.2 A/s agglom eration would be much less. Therefore, one can expect LSC to occur at an earlier stage itself as the degree of agglom eration determ ines the thickness at which Im tends to become continuous [12]. However, insulator { metal transition occurring after the stoppage of deposition is a fascinating new result.

The insulator { metal transition in a conservative system may be explained as follows. At very low deposition rates, not only LSC occurs at an early stage of deposition, but, due to reduced agglom eration, very little material is required to connect the large network to establish a percolation path between the electrodes. The incorporation of secondary nuclei into the network structure due to their mobility may result in a percolation path leading to an insulator metal transition. This cannot be expected in a more agglom – erated Im deposited at higher deposition rates as more material is required to establish a percolation path and just the incorporation of secondary nuclei would not be su cient for this purpose. As a consequence, insulator { metal transition after the stoppage of deposition is not observed for Im s deposited at higher rates (eq. R ef. 10)

The other interesting feature is that the transition is not a gradual decrease of resistance but a sudden one and is preceded by uctuations in resistance with time. These uctuations in resistance can, in principle, be due to the dynamic uctuations in the average island spacing. But, such dynamic

uctuations in average island spacing due to the mobility of islands should always be present, not only in the vicinity of insulator - m etal transition. Under the conditions that are not leading to such a transition, the variation of resistance with time were always found to be smooth. On the other hand, these uctuations can be due to the making and breaking of the circuit or the



Figure 1: The variation of resistance with time after the stoppage of deposition for a Silver m of thickness 100A

conducting paths between the networks. The decrease in resistance is due to the lling up of the gaps between the networks by the secondary nuclei. The gaps lled by these secondary nuclei forms a weak electrical link between two large networks. The typical size of secondary nuclei can be from a few to a few tens of nanom eters. The current used by the resistance-m easuring instrum ent used in the present studies (K eithley Electrom eter model 617) is only of the order of microam peres. But still, the current density owing through these weak links would be very large ( $10^{6}$ A/cm<sup>2</sup> for the 10 nm cluster) and can cause the catastrophic destruction of these weak links. This would give rise to the breaking of the conduction paths established, increasing the lm resistance. At the onset of insulator -m etal transition, a large num ber of parallel conducting paths between the electrodes are established and therefore, the current density gets distributed, avoiding the destruction of the weak links. Therefore, the lm resistance remains steady after the transition.

## Conclusions:

The conclusions that can be drawn from the aging studies of silver island lm s can be summarized as follow s:

1. The e ect of various parameters on the aging rates of Silver Island Im s suggest that the mobility of islands followed by coalescence is responsible for aging in these Im s.

2. An interesting insulator -m etal transition is observed under certain conditions in silver m s, long after the stoppage of deposition. This is attributed to the establishment of metallic conduction paths due to the incorporation of secondary nuclei to the network structure. The transition is preceded by large uctuations in resistance.

3. The uctuations in Im resistance is attributed to the form ation of conduction paths and their breakage due to the passage of high current density at the weak links in the path.

4. The insulator-m etal transition observed in a conservative system is a clear evidence for the m obility of islands.

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